

Recipe	N-Al2O3_All_Half	O - Al Etch_25C	O - HfO2_etch	O-SiNx_Etch	O-SiO2_Etch (PR_Mask)	N-ZnO_Etch	O - SiO2 RIE Mode
Film							
Si	1000	2100	1600				
SiO2	910	775 or 910	1800		3633	11193	
Nit	515	900	1300 *	4700	1800	3400 or 3600	800
LSN	630	1275	1500	3440	1700	1550	300
Resist	735	4000				3047	
Poly Silicon							
PECVD Oxide							
PECVD Nit							
Al2O3	700	500	1300	140			
HfO2			750				
ZnO						332	
TiO2							
Al		3933					
Ti							
Nb							
Cr							

* With 10 min conditioning run, varies greatly (~300 Angstroms/min) from run to run

All values listed are in Angstroms / min. These values are a guide only. To get best results confirm etch rate for your sample yourself.